

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1 (currently amended) A slurry for chemical mechanical polishing (CMP) a metal surface of a semiconductor substrate with a polyurethane free thermoplastic foam polishing body, comprising,

an acid buffer that maintains said slurry at a pH between about 2.5 and about 4.0 during polishing of a metal surface on a semiconductor substrate; and

an abrasive particle stabilizer, wherein said abrasive particle stabilizer comprises molecules that are equivalent to repeating units of polymers comprising abrasive particles in said slurry

wherein said abrasive particles comprise colloidal silica particles and said abrasive particle stabilizer comprises silicic acid and silicic salt and a ratio of said silicic acid to said silicic salt is between about 100:1 and 1:100.

2 (original) The slurry as recited in Claim 1, wherein said pH is between about 2.7 and about 3.2.

3. (original) The slurry as recited in Claim 1, wherein said pH is between about 3.5 and about 4.0.

Claim 4-7 (canceled)

8. (original) The slurry as recited in Claim 1, further including an oxidant and a passivation agent.

9. (original) The slurry as recited in Claim 8, wherein said passivation agent is generated in situ from a reaction between said metal surface and said oxidant.

10. (original) The slurry as recited in Claim 9, wherein said oxidant is potassium iodate ( $KIO_3$ ) said passivation agent is iodine ( $I_2$ ) and said metal surface includes copper.

11. (original) The slurry as recited in Claim 9, further including a second passivation agent that is not generated *in situ* wherein said passivation agent and said second passivation agent synergistically interact with said metal surface to retard corrosion of said metal surface.

Claim 12-20 (canceled)